

STTH60W02C

Turbo 2 ultrafast high voltage rectifier

Datasheet - production data

Features

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK[®]2 compliant component
- Ribbon bonding for more robustness

Description

The STTH60W02CW uses ST Turbo 2, 200 V technology. It is especially suited for use in DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

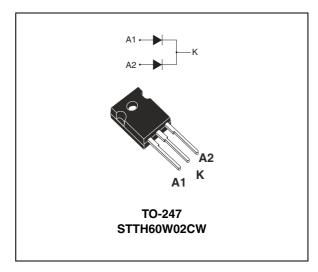


Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 30 A
V _{RRM}	200 V
t _{rr} (typ)	24 ns
T _j (max)	175 °C
V _F (typ)	0.85 V

Characteristics STTH60W02C

1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, per diode)

Symbol	Paramete	Value	Unit			
V_{RRM}	Repetitive peak reverse voltage			200	V	
I _{F(RMS)}	Forward rms current			45	Α	
1	Average forward current, $\delta = 0.5$	T _c = 125 °C	Per diode	30	Α	
$I_{F(AV)}$ Average forward current, $\delta = 0$.	Average forward current, $\delta = 0.5$	T _c = 115°C	Per device	60	^	
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sin}$	250	Α		
T _{stg}	Storage temperature range	-65 to + 175	°C			
T _j	Maximum operating junction temperature			+ 175	°C	

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit		
В	Junction to case	Per diode	1.3	°C / W	
R _{th(j-c)}	Junction to case	Total	0.8	C / VV	
R _{th(c)}	Coupling		0.3	°C/W	

When diodes 1 and 2 are used simultaneously:

 $T_{j}(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾ Reverse leakage current	Poverce leakage current	T _j = 25 °C	V V			10	
	T _j = 125 °C	$V_R = V_{RRM}$		10	100	μΑ	
	V (2) Famurad valtage dues	T _j = 25 °C	I _F = 30A			1.15	V
V _F ⁽²⁾		T _j = 150 °C			0.85	1.0	
V _F ⁽²⁾ Forward voltage drop	Forward voltage drop	T _j = 25 °C	I _F = 60 A			1.35	V
		T _j = 150 °C			1.05	1.25	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.75 \text{ x } I_{F(AV)} + 0.0083 I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

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 Table 5.
 Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _{RM}	Reverse recovery current		1 00 4 1/ 100 1/		8	10.5	Α
Q _{RR}	Reverse recovery charge	T _j = 125 °C	$I_F = 30 \text{ A}, V_R = 160 \text{ V}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$		220		nC
S _{factor}	Softness factor				0.3		
t _{rr}	Reverse recovery time	T _j = 25 °C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}$ $dI_F/dt = -100 \text{ A/}\mu\text{s}$		24	30	ns
t _{fr}	Forward recovery time	$T_j = 25 ^{\circ}\text{C}$ $I_F = 30 \text{A}, V_{FR} = 1.1 \text{V}$				300	ns
V _{FP}	Forward recovery voltage	T _j = 25 °C	dI _F /dt = 200 A/μs		2	3	V

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current (per diode) forward current (per diode)

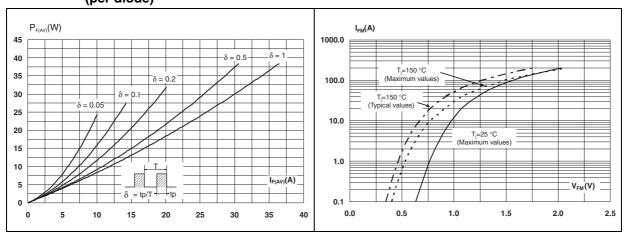


Figure 3. Relative variation of thermal Figure 4. impedance junction to case versus pulse duration

diode)

IRM(A)

18
16 V_{n=160 V}
T_{i=125 °C}
14
12
10
8
6
4
2
0
0 50 100 150 200 250 300 350 400 450 500

Peak reverse recovery current

versus dl_F/dt (typical values, per

Zth(j-c)/Rth(j-c)

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

Single pulse

0.2

0.1

tp(s)

1.E-01

0.0 -1.E-04 Characteristics STTH60W02C

Figure 5. Reverse recovery time versus dl_F/dt Figure 6. Reverse recovery charges versus (typical values, per diode) dl_F/dt (typical values, per diode)

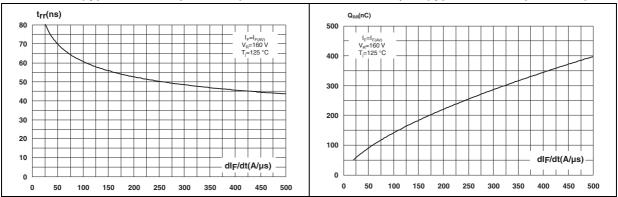


Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)

Figure 8. Relative variation of dynamic parameters versus junction temperature

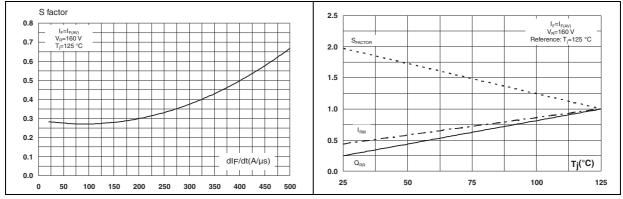
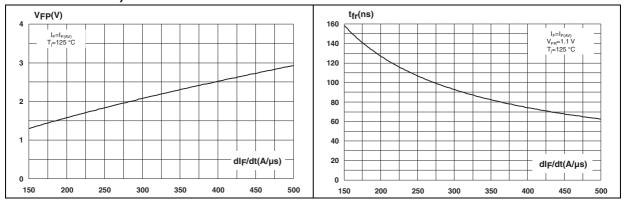


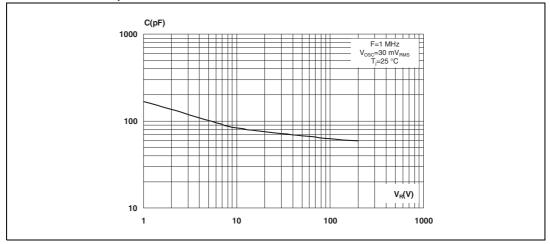
Figure 9. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

Figure 10. Forward recovery time versus dl_F/dt (typical values, per diode)



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Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



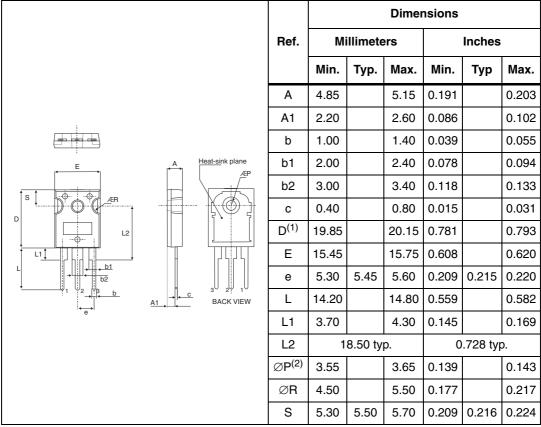
Package information STTH60W02C

2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-247 dimensions



- 1. Dimension D plus gate protrusion does not exceed 20.5 mm
- 2. Resin thickness around the mounting hole is not less than 0.9 mm

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode	
STTH60W02CW	STTH60W02CW	TO-247	4.46 g	50	Tube	

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-Oct-2012	1	First issue.

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